



AOS Semiconductor Product Reliability Report

AOZ8001KIL, rev A

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

**495 Mercury Drive
Sunnyvale, CA 94085
U.S.**

Tel: (408) 830-9742

www.aosmd.com



This AOS product reliability report summarizes the qualification result for AOZ8001KIL.

Review of the electrical test results confirm that AOZ8001KIL pass AOS quality and reliability requirements for product release. The continuous qualification testing and reliability monitoring program ensure that all outgoing products will continue to meet AOS quality and reliability standards.

Table of Contents:

- I. Product Description
- II. Package and Die information
- III. Qualification Test Requirements
- IV. Qualification Tests Result
- V. Reliability Evaluation

I. Product Description:

The AOZ8001KIL is a transient voltage suppressor array to protect high speed data lines from ESD and lightning.

| Absolute Maximum Ratings | |
|---|-----------------|
| Parameter | |
| VP-VN | 6v |
| Peak Pulse Current (Ipp), tp=8/20uS | 5A |
| Storage Temperature (Ts) | -65°C to +150°C |
| ESD Rating per IEC61000-4-2, contact ⁽¹⁾ | ±8kV |
| ESD Rating per IEC61000-4-2, air ⁽²⁾ | ±15kV |
| ESD Rating per Human Body Model ⁽²⁾ | ±15kV |
| Junction Temperature (Tj) | -40°C to +85°C |

Notes:

- (1) IEC-61000-4-2 discharge with $C_{Discharge}=150pF$, $R_{Discharge}=330\Omega$
- (2) Human Body Discharge per MIL-STD-883, Method 3015 $C_{Discharge}=100pF$, $R_{Discharge}=1.5k\Omega$

II. Package and Die Information:

| | |
|---------------------|---------------|
| Product ID | AOZ8001KIL |
| Process | HHNEC HV003A1 |
| Package Type | SC89A |
| Lead Frame | Cu |
| Die attach material | 8006NS |
| Die bond wire | Au, 1 mil |
| Mold Material | E670CB |
| MSL level | Up to Level 1 |

III. Qualification Tests Requirements

- 2 lots of AOZ8001KIL up to 500 hrs of HTOL for New Product release.
- 3 lots of package qual testing (PCT, 500 cycles TC, HAST) for package release to manufacturing.

IV. Qualification Tests Result

| Test Item | Test Condition | Sample Size | Result | Comment |
|------------------------|--|------------------|--------|---------------|
| Pre-Conditioning | Per JESD 22-A113 168hrs @85 °C /85%RH+3 cyc reflow@260°C | 3 lots | pass | |
| HTOL | Per JESD 22-A108_B Vdd= 6v Temp = 125°C | 2 lots (80 /lot) | pass | |
| Temperature Cycle | '-65 °C to +150 °C, air to air (2cyc/hr) | 3 lots (82 /lot) | pass | |
| Pressure Pot | 121°C, 29.7psi, RH= 100% | 3 lots (82 /lot) | pass | |
| HAST | '130 +/- 2°C, 85%RH, 33.3 psi, at VCC min power dissipation. | 3 lots (60 /lot) | pass | |
| ESD Rating | Per IEC-61000-4-2, contact | 3 lots (5 /lot) | pass | ±8kV contact |
| ESD Rating | Per IEC-61000-4-2, air discharge | 3 lots (5 /lot) | pass | ±15kV contact |
| Lightning Surge rating | Per IEC-61000-4-5 | 3 lots (5 /lot) | pass | 5A surge |

The qualification test results confirm that AOZ8001KIL pass AOS quality and reliability requirements for product release.

V. Reliability Evaluation

FIT rate (per billion): 44

MTTF = 2575 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion device hours.

$$\text{Failure Rate} = \text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)] = 1.83 \times 10^9 / [2 \times 2 \times 80 \times 500 \times 258] = 44$$

$$\text{MTTF} = 10^9 / \text{FIT} = 2.26 \times 10^7 \text{hrs} = 2575 \text{ years}$$

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [**Af**] = **Exp** [Ea / k (1/Tj u - 1/Tj s)]

Acceleration Factor ratio list:

| | 55 deg C | 70 deg C | 85 deg C | 100 deg C | 115 deg C | 130 deg C | 150 deg C |
|-----------|------------|-----------|-----------|-----------|-------------|-------------|-----------|
| Af | 258 | 87 | 32 | 13 | 5.64 | 2.59 | 1 |

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C+273.16

k = Boltzmann's constant, 8.617164 X 10⁻⁵eV / K